### Composite Transistors

# **Panasonic**

# XP04878

## Silicon N-channel MOSFET

#### For switching

#### Features

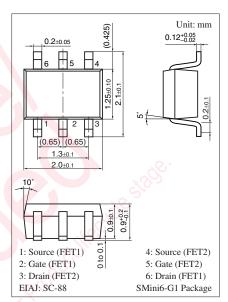
- Allowing 2.5 V drive
- Incorporating a built-in gate protection-diode
- S-Mini type 6-pin package, reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• 2SK3539 × 2

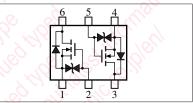
#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

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Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	50	V
Gate-source voltage (Drain open)	V <sub>GSO</sub>	±7	V
Drain current	ID	100	mA
Peak drain current	I <sub>DP</sub>	200	mA
Total power dissipation	P <sub>T</sub>	150	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C
			1 1



#### Marking Symbol: 7Y

#### Internal Connection



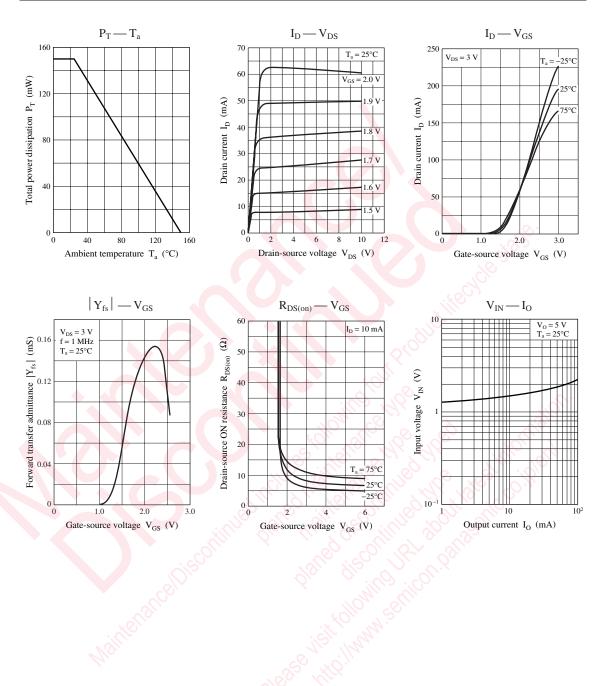
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	$I_{\rm D} = 10 \ \mu A, \ V_{\rm GS} = 0$	50			V
Drain-source cutoff current	I <sub>DSS</sub>	$V_{DS} = 50 \text{ V},  \text{V}_{GS} = 0$			1.0	μΑ
Gate-source cutoff current	I <sub>GSS</sub>	$V_{GS} = \pm 7 V, V_{DS} = 0$			±5	μΑ
Gate threshold voltage	V <sub>th</sub>	$I_D = 1 \ \mu A, \ V_{DS} = 3 \ V$	0.9	1.2	1.5	V
Drain-source ON resistance	R <sub>DS(on)</sub>	$I_{\rm D} = 10 \text{ mA}, \text{ V}_{\rm GS} = 2.5 \text{ V}$		8	15	Ω
		$I_{\rm D} = 10 \text{ mA}, V_{\rm GS} = 4.0 \text{ V}$		6	12	
Forward transfer admittance	Y <sub>fs</sub>	$I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$	20	60		mS
Short-circuit forward transfer capacitance (Common-source)	C <sub>iss</sub>	$V_{DS} = 3 V, V_{GS} = 0 V, f = 1 MHz$		12		pF
Short-circuit output capacitance (Common-source)	C <sub>oss</sub>	-		7		pF
Reverse transfer capacitance (Common-source)	C <sub>rss</sub>			3		pF
Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, V_{GS} = 0 \text{ V} \text{ to } 3 \text{ V}, R_L = 470 \Omega$		200		ns
Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, V_{GS} = 3 \text{ V} \text{ to } 0 \text{ V}, R_L = 470 \Omega$		200		ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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